## Product Preview

# Low-Voltage CMOS Octal Buffer Flow Through Pinout

# With 5 V-Tolerant Inputs and Outputs (3-State, Non-Inverting)

The 74LVC541A is a high performance, non–inverting octal buffer operating from a 1.2 to 3.6 V supply. This device is similar in function to the MC74LCX244, while providing flow through architecture. High impedance TTL compatible inputs significantly reduce current loading to input drivers while TTL compatible outputs offer improved switching noise performance. A V<sub>I</sub> specification of 5.5 V allows 74LVC541A inputs to be safely driven from 5 V devices. The 74LVC541A is suitable for memory address driving and all TTL level bus oriented transceiver applications.

Current drive capability is 24 mA at the outputs. The Output Enable  $(\overline{OE1}, \overline{OE2})$  inputs, when HIGH, disables the output by placing them in a HIGH Z condition.

### **Features**

- Designed for 1.2 to 3.6 V V<sub>CC</sub> Operation
- 5 V Tolerant Interface Capability With 5 V TTL Logic
- Supports Live Insertion and Withdrawal
- $I_{OFF}$  Specification Guarantees High Impedance When  $V_{CC} = 0 V$
- 24 mA Output Sink and Source Capability
- Near Zero Static Supply Current in All Three Logic States (10 μA)
   Substantially Reduces System Power Requirements
- Latchup Performance Exceeds 250 mA
- ESD Performance:
  - ♦ Human Body Model > 2000 V
  - ♦ Machine Model > 200 V
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant



## ON Semiconductor®

www.onsemi.com





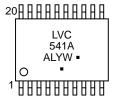


TSSOP-20 DT SUFFIX CASE 948E

#### MARKING DIAGRAMS



SOIC-20 WB



TSSOP-20

A = Assembly Location

L, WL = Wafer Lot Y, YY = Year W, WW = Work Week G or = Pb-Free Package

(Note: Microdot may be in either location)

### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 7 of this data sheet.

This document contains information on a product under development. ON Semiconductor reserves the right to change or discontinue this product without notice.

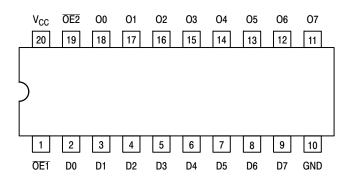


Figure 1. Pinout: 20-Lead (Top View)

## **PIN NAMES**

Pins	Function
<del>OEn</del>	Output Enable Inputs
Dn	Data Inputs
On	3-State Outputs

## **TRUTH TABLE**

Inputs			Outputs		
OE1	OE2	Dn	On		
L	L	L	L		
L	L	Н	Н		
Х	Н	Х	Z		
Н	Х	Х	Z		

H = High Voltage Level; L = Low Voltage Level; Z = High Impedance State; X = High or Low Voltage Level and Transitions are Acceptable, for  $I_{CC}$  reasons, DO NOT FLOAT Inputs

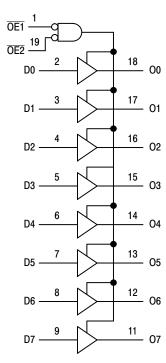


Figure 2. Logic Diagram

## **MAXIMUM RATINGS**

Symbol	Parameter	Value	Condition	Unit
V <sub>CC</sub>	DC Supply Voltage	-0.5 to +6.5		V
VI	DC Input Voltage	$-0.5 \le V_1 \le +6.5$		V
Vo	DC Output Voltage	$-0.5 \le V_{O} \le +6.5$	Output in 3-State	V
		$-0.5 \le V_{O} \le V_{CC} + 0.5$	Output in HIGH or LOW State (Note 1)	V
I <sub>IK</sub>	DC Input Diode Current	-50	V <sub>I</sub> < GND	mA
I <sub>OK</sub>	DC Output Diode Current	-50	V <sub>O</sub> < GND	mA
		+50	V <sub>O</sub> > V <sub>CC</sub>	mA
Io	DC Output Source/Sink Current	±50		mA
Icc	DC Supply Current Per Supply Pin	±100		mA
I <sub>GND</sub>	DC Ground Current Per Ground Pin	±100		mA
T <sub>STG</sub>	Storage Temperature Range	-65 to +150		°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds	T <sub>L</sub> = 260		°C
TJ	Junction Temperature Under Bias	T <sub>J</sub> = 135		°C
$\theta_{JA}$	Thermal Resistance (Note 2)	SOIC = 65.8 TSSOP = 110.7		°C/W
MSL	Moisture Sensitivity		Level 1	
I <sub>LATCHUP</sub>	Latch-up Performance at V <sub>CC</sub> = 3.6 V and 125°C (Note 3)		±250	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- I<sub>O</sub> absolute maximum rating must be observed.
   Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2 ounce copper trace no air flow.
- 3. Tested to EIA/JES078.

## **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Min	Тур	Max	Units
V <sub>CC</sub>	Supply Voltage Operating Functional	1.65 1.2		3.6 3.6	V
VI	Input Voltage	0		5.5	V
V <sub>O</sub>	Output Voltage HIGH or LOW State 3-State	0		V <sub>CC</sub> 5.5	V
I <sub>OH</sub>	HIGH Level Output Current V <sub>CC</sub> = 3.0 V - 3.6 V V <sub>CC</sub> = 2.7 V - 3.0 V			-24 -12	mA
I <sub>OL</sub>	LOW Level Output Current V <sub>CC</sub> = 3.0 V - 3.6 V V <sub>CC</sub> = 2.7 V - 3.0 V			24 12	mA
T <sub>A</sub>	Operating Free–Air Temperature	-40		+125	°C
Δt/ΔV	Input Transition Rise or Fall Rate, V <sub>IN</sub> from 0.8 V to 2.0 V, V <sub>CC</sub> = 3.0 V	0		10	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

## DC ELECTRICAL CHARACTERISTICS

			-4	0°C to +8	5°C	-40	°C to +12	5°C	
Symbol	Parameter	Conditions	Min	Typ (Note 4)	Max	Min	Typ (Note 4)	Max	Unit
VIH	HIGH-level input	V <sub>CC</sub> = 1.2 V	1.08	-	-	1.08	-	-	V
	voltage	V <sub>CC</sub> = 1.65 V to 1.95 V	0.65 x V <sub>CC</sub>	_	-	0.65 x V <sub>CC</sub>	-	_	
		V <sub>CC</sub> = 2.3 V to 2.7 V	1.7	-	-	1.7	-	-	
		$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	2.0	-	-	2.0	_	-	
$V_{IL}$	LOW-level input	V <sub>CC</sub> = 1.2 V	-	-	0.12	-	-	0.12	V
	voltage	V <sub>CC</sub> = 1.65 V to 1.95 V	-	_	0.35 x V <sub>CC</sub>	_	-	0.35 x V <sub>CC</sub>	
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	-	0.7	-	-	0.7	
		V <sub>CC</sub> = 2.7 V to 3.6 V	-	-	0.8	-	-	0.8	
V <sub>OH</sub>	HIGH-level output	$V_I = V_{IH}$	or V <sub>IL</sub>						V
	voltage	$I_O = -100 \mu A;$ $V_{CC} = 1.65 \text{ V to } 3.6 \text{ V}$	V <sub>CC</sub> - 0.2	_	-	V <sub>CC</sub> - 0.3	-	-	
		$I_O = -4 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.2	-	-	1.05	-	-	
		$I_{O} = -8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.8	-	-	1.65	-	_	
		$I_O = -12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	2.2	-	-	2.05	-	-	
		$I_O = -18 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.4	-	-	2.25	-	-	
		$I_O = -24$ mA; $V_{CC} = 3.0$ V	2.2	-	-	2.0	-	-	
VOL	LOW-level output	$V_I = V_{IH}$	or V <sub>IL</sub>						V
	voltage	$I_O = 100 \mu A;$ $V_{CC} = 1.65 \text{ V to } 3.6 \text{ V}$	-	_	0.2	_	-	0.3	
		I <sub>O</sub> = 4 mA; V <sub>CC</sub> = 1.65 V	-	_	0.45	_	_	0.65	
		$I_O = 8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	_	0.6	_	_	0.8	
		$I_{O} = 12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	-	-	0.4	-	-	0.6	
		$I_O = -24 \text{ mA}; V_{CC} = 3.0 \text{ V}$	ı	-	0.55	-	_	0.8	
I <sub>I</sub>	Input leakage current	$V_I = 5.5 \text{V}$ or GND $V_{CC} = 3.6 \text{ V}$	ı	±0.1	±5	-	±0.1	±20	μΑ
l <sub>OZ</sub>	OFF-state output current	VI = VIH  or  VIL; $V_O = 5.5 \text{ V or GND}; V_{CC} = 3.6 \text{ V}$	-	±0.1	±5	_	±0.1	±20	μΑ
l <sub>OFF</sub>	Power-off leakage current	$V_{I}$ or $V_{O} = 5.5 \text{ V}$ ; $V_{CC} = 0.0 \text{ V}$	-	±0.1	±10	_	±0.1	±20	μА
Icc	Supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 3.6 \text{ V}$	-	0.1	10	_	0.1	40	μΑ
Δl <sub>CC</sub>	Additional supply current	per input pin; $V_1 = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A};$ $V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	-	5	500	-	5	5000	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. All typical values are measured at  $T_A = 25^{\circ}C$  and  $V_{CC} = 3.3$  V, unless stated otherwise.

## AC ELECTRICAL CHARACTERISTICS ( $t_R = t_F = 2.5 \text{ ns}$ )

			-40°C to +85°C		5°C	-40°	°C to +12	25°C	
Symbol	Parameter	Conditions	Min	Typ <sup>1</sup>	Max	Min	Typ <sup>1</sup>	Max	Unit
t <sub>pd</sub>	Propagation Delay (Note 6) nAn to nYn	V <sub>CC</sub> = 1.2 V	_	14.0	_	-	_	-	ns
	MAN TO NYN	V <sub>CC</sub> = 1.65 V to 1.95 V	1.5	6.5	13.8	1.5	-	16.0	
		V <sub>CC</sub> = 2.3 V to 2.7 V	1.0	3.5	6.8	1.0	-	7.9	
		V <sub>CC</sub> = 2.7 V	1.5	3.5	5.6	1.5	-	7.0	
		V <sub>CC</sub> = 3.0 V to 3.6 V	1.0	2.9	5.1	1.0	-	6.5	
t <sub>en</sub>	Enable Time (Note 7)	V <sub>CC</sub> = 1.2 V	_	20.0	-	-	-	-	ns
	nOE to nYn	V <sub>CC</sub> = 1.65 V to 1.95 V	1.8	7.7	16.0	1.8	-	18.5	
		V <sub>CC</sub> = 2.3 V to 2.7 V	1.5	4.3	8.8	1.5	-	10.2	
		V <sub>CC</sub> = 2.7 V	1.5	4.4	7.5	1.5	-	9.5	
		V <sub>CC</sub> = 3.0 V to 3.6 V	1.0	3.5	7.0	1.0	-	9.0	
t <sub>dis</sub>	Disable Time (Note 8)	V <sub>CC</sub> = 1.2 V	_	11.0	-	-	-	-	ns
	nOE to nYn	V <sub>CC</sub> = 1.65 V to 1.95 V	3.0	4.9	10.3	3.0	-	11.9	
		V <sub>CC</sub> = 2.3 V to 2.7 V	1.0	2.7	5.9	1.0	-	6.8	
		V <sub>CC</sub> = 2.7 V	1.5	3.7	7.0	1.5	_	9.0	
		V <sub>CC</sub> = 3.0 V to 3.6 V	1.0	3.3	6.0	1.0	_	7.5	
t <sub>sk(0)</sub>	Output Skew Time (Note 9)		_	-	1	-	-	1.5	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- 5. Typical values are measured at TA = 25°C and Vcc = 3.3 V, unless stated otherwise.
- 6. t<sub>pd</sub> is the same as t<sub>PLH</sub> and t<sub>PHL</sub>.
- 7. t<sub>en</sub> is the same as t<sub>PZL</sub> and t<sub>PZH</sub>.
- 8.  $t_{dis}$  is the same as  $t_{PLZ}$  and  $t_{PHZ}$ .
- 9. Skew between any two outputs of the same package switching in the same direction. This parameter is guaranteed by design.

### **DYNAMIC SWITCHING CHARACTERISTICS**

			T <sub>A</sub> = +25°C			
Symbol	Characteristic	Condition	Min	Тур	Max	Unit
V <sub>OLP</sub>	Dynamic LOW Peak Voltage (Note 10)	$\begin{array}{c} V_{CC} = 3.3 \text{ V, } C_L = 50 \text{ pF, } V_{IH} = 3.3 \text{ V, } V_{IL} = 0 \text{ V} \\ V_{CC} = 2.5 \text{ V, } C_L = 30 \text{ pF, } V_{IH} = 2.5 \text{ V, } V_{IL} = 0 \text{ V} \end{array}$		0.8 0.6		V
V <sub>OLV</sub>	Dynamic LOW Valley Voltage (Note 10)	$\begin{aligned} &V_{CC} = 3.3 \text{ V, } C_L = 50 \text{ pF, } V_{IH} = 3.3 \text{ V, } V_{IL} = 0 \text{ V} \\ &V_{CC} = 2.5 \text{ V, } C_L = 30 \text{ pF, } V_{IH} = 2.5 \text{ V, } V_{IL} = 0 \text{ V} \end{aligned}$		-0.8 -0.6		V

<sup>10.</sup> Number of outputs defined as "n". Measured with "n-1" outputs switching from HIGH-to-LOW or LOW-to-HIGH. The remaining output is measured in the LOW state.

## **CAPACITIVE CHARACTERISTICS**

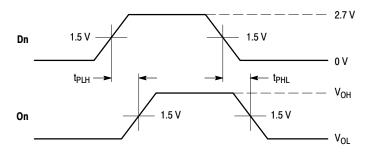
Symbol	Parameter	Condition	Typical	Unit	
CIN	Input Capacitance	$V_{CC} = 3.3 \text{ V}, V_{I} = 0 \text{ V or } V_{CC}$	4.0	pF	
Соит	Output Capacitance	$V_{CC} = 3.3 \text{ V}, V_{I} = 0 \text{ V or } V_{CC}$	5.0	pF	
$C_{PD}$	Power Dissipation Capacitance	Per input; $V_I = GND$ or $V_{CC}$			
	(Note 11)	V <sub>CC</sub> = 1.65 V to 1.95 V	7.7		
		V <sub>CC</sub> = 2.3 V to 2.7 V	11.3		
		V <sub>CC</sub> = 3.0 V to 3.6 V	14.4		

<sup>11.</sup>  $C_{PD}$  is used to determine the dynamic power dissipation ( $P_D$  in  $\mu W$ ).

 $P_D = C_{PD} * V_{CC}^2 x fi * N + \Sigma (C_L x V_{CC}^2 x fo)$  where: fi = input frequency in MHz; fo = output frequency in MHz

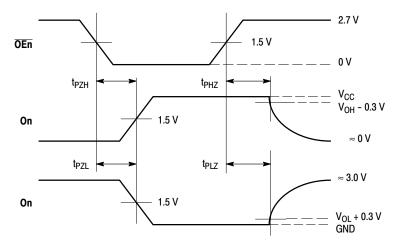
 $C_L$  = output load capacitance in pF  $V_{CC}$  = supply voltage in Volts

N = number of outputs switching  $\Sigma(C_L * V_{CC}^2 x \text{ fo})$  = sum of the outputs.



## **WAVEFORM 1 - PROPAGATION DELAYS**

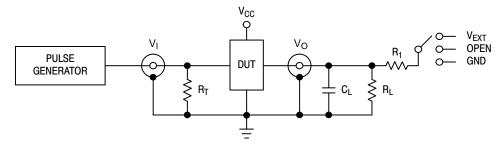
 $t_R$  =  $t_F$  = 2.5 ns, 10% to 90%; f = 1 MHz;  $t_W$  = 500 ns



# $\label{eq:waveform 2-output enable and disable times} $t_R = t_F = 2.5 \text{ ns, } 10\% \text{ to } 90\%; f = 1 \text{ MHz; } t_W = 500 \text{ ns}$

Figure 3. AC Waveforms

	V <sub>CC</sub>						
Symbol	3.3 V $\pm$ 0.3 V	2.7 V	V <sub>CC</sub> < 2.7 V				
Vmi	1.5 V	1.5 V	V <sub>CC</sub> /2				
Vmo	1.5 V	1.5 V	V <sub>CC</sub> /2				
V <sub>HZ</sub>	V <sub>OL</sub> + 0.3 V	V <sub>OL</sub> + 0.3 V	V <sub>OL</sub> + 0.15 V				
$V_{LZ}$	V <sub>OH</sub> – 0.3 V	V <sub>OH</sub> – 0.3 V	V <sub>OH</sub> – 015 V				



 $C_L$  includes jig and probe capacitance  $R_T$  =  $Z_{OUT}$  of pulse generator (typically 50  $\Omega)$   $R_1$  =  $R_L$ 

Supply Voltage	Input		Load		V <sub>EXT</sub>		
V <sub>CC</sub> (V)	VI	t <sub>r</sub> , t <sub>f</sub>	CL	R <sub>L</sub>	t <sub>PLH</sub> , t <sub>PHL</sub>	t <sub>PLZ</sub> , t <sub>PZL</sub>	t <sub>PHZ</sub> , t <sub>PZH</sub>
1.2	V <sub>CC</sub>	≤ 2 ns	30 pF	1 kΩ	Open	2 x V <sub>CC</sub>	GND
1.65 – 1.95	V <sub>CC</sub>	≤ 2 ns	30 pF	1 kΩ	Open	2 x V <sub>CC</sub>	GND
2.3 – 2.7	V <sub>CC</sub>	≤ 2 ns	30 pF	500 Ω	Open	2 x V <sub>CC</sub>	GND
2.7	2.7 V	≤ 2.5 ns	50 pF	500 Ω	Open	2 x V <sub>CC</sub>	GND
3 – 3.6	2.7 V	≤ 2.5 ns	50 pF	500 Ω	Open	2 x V <sub>CC</sub>	GND

Figure 4. Test Circuit

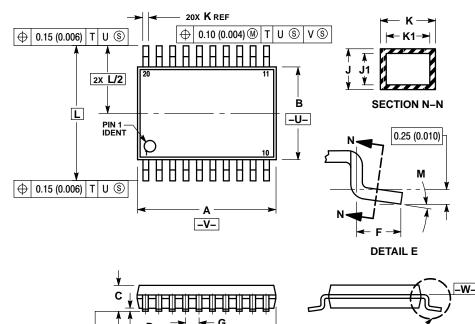
## **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>	
74LVC541ADWR2G	SOIC-20 (Pb-Free)	1000 / Tape & Reel	
74LVC541ADTR2G	TSSOP-20 (Pb-Free)	2500 / Tape & Reel	

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

### PACKAGE DIMENSIONS

## TSSOP-20 CASE 948E-02 **ISSUE C**



☐ 0.100 (0.004) -T- SEATING

#### NOTES:

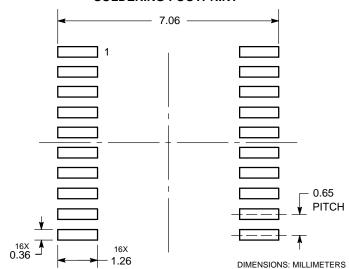
- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER.

- MILLIMETER.
  3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
  4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
  5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K
- (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL
- CONDITION.
  6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
  7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	6.40	6.60	0.252	0.260	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026 BSC		
Н	0.27	0.37	0.011	0.015	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40		0.252 BSC		
M	0°	8°	0°	8°	

## **SOLDERING FOOTPRINT\***

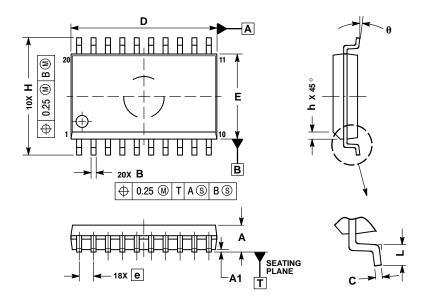
**DETAIL E** 



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

## PACKAGE DIMENSIONS

## SOIC-20 WB CASE 751D-05 ISSUE G



#### NOTES:

- DIMENSIONS ARE IN MILLIMETERS.
  INTERPRET DIMENSIONS AND TOLERANCES
  PER ASME Y14.5M, 1994.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD
- MAXIMUM MOLD PROTRUSION 0.15 PER SIDE. DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS	
DIM	MIN	MAX
Α	2.35	2.65
A1	0.10	0.25
В	0.35	0.49
С	0.23	0.32
D	12.65	12.95
Е	7.40	7.60
е	1.27 BSC	
Н	10.05	10.55
h	0.25	0.75
L	0.50	0.90
θ	0 °	7°

ON Semiconductor and the 👊 are registered trademarks of Semiconductor Components Industries, LLC (SCILLC) or its subsidiaries in the United States and/or other countries. SCILLC owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of SCILLC's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and or guarantee regarding the solitability or its products of any particular purpose, not does of science any liability anising out of the application in set of any product of clictur, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patient rights or then rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses and reasonable attroney fees arising out of directive any design of personal injury or death escapital with such unjustended or unauthorized deprivations. expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

## **PUBLICATION ORDERING INFORMATION**

#### LITERATURE FULFILLMENT

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA

Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

Japan Customer Focus Center

Phone: 81-3-5817-1050

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative